

MSH16120G1

1200V Silicon Carbide Schottky Diode

Features

- 1200-Volt Schottky Rectifier
- Shorter recovery time
- High-speed switching possible
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Extremely Fast Switching
- Positive Temperature Coefficient on VF

Benefits

- Higher safety margin against overvoltage
- Improved efficiency all load conditions
- Increased efficiency compared to Silicon Diode alternatives
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway
- Essentially No Switching Losses

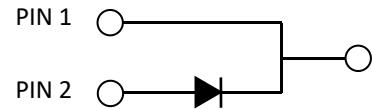
Applications

- Switch Mode Power Supplies
- Power Factor Correction
- Motor Drives
- HID Lighting

Package



Type : TO-247-2Lead



Absolute Maximum Ratings

$T_c = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	MSH20120G1	Units
VRRM	Repetitive Peak Reverse Voltage	1200	V
VRSM	Surge Peak Reverse Voltage	1200	V
VDC	DC Blocking Voltage	1200	V
IF	Continuous Forward Current @ $T_c=150^\circ\text{C}$	15	A
IFRM	Repetitive Peak Forward Surge Current @ $T_c=25^\circ\text{C}$, $t_P = 10\text{ ms}$, Half Sine Wave	80	A
IFSM	Non-Repetitive Peak Forward Surge Current (Per Leg) @ $T_c=25^\circ\text{C}$, $t_P = 10\text{ ms}$, Half Sine Wave	120	A
IF,Max	Non-Repetitive Peak Forward Surge Current ;@ $T_c=25^\circ\text{C}$, $t_P = 10\ \mu\text{s}$, Pulse	850	A
Ptot	Power Dissipation (Per Leg/Device) @ $T_c=25^\circ\text{C}$ @ $T_c=110^\circ\text{C}$	258 112	W
$\int i^2 dt$	I^2t value, $T_c=25^\circ\text{C}$	72	A^2s
T_J, T_{stg}	Operating Junction and Storage Temperature	-55 to +175	$^\circ\text{C}$

Electrical Characteristics

T_C = 25° C unless otherwise noted

Symbol	Test Conditions	Test Conditions	Min	Typ	Max	Unit
VF	Forward Voltage(Per Lag)	IF=15A, TC=25° C IF=15A, TC=175° C	-	1.5 2.2	1.8 2.5	V
IR	Reverse Current	VR=1200V, TC=25° C VR=1200V, TC=175° C	-	10 20	50 100	μA
QC	Total Capacitive Charge	VR =800V, TJ = 25° C Qc= $\int_0^{t_r} C (V) dv$	-	78	-	nC
C	Total Capacitance	VR =0V, TJ = 25° C, f=1MHz VR =400V, TJ = 25° C, f=1MHz VR =800V, TJ = 25° C, f=1MHz	-	1090 70 53	-	pF
EC	Capacitance Stored Energy	VR=800V	-	40	-	μJ

Thermal Characteristics

Symbol	Parameter	Typ	Unit
RθJC	Thermal Resistance from Junction to Case	0.58	°C/W

Typical Characteristics

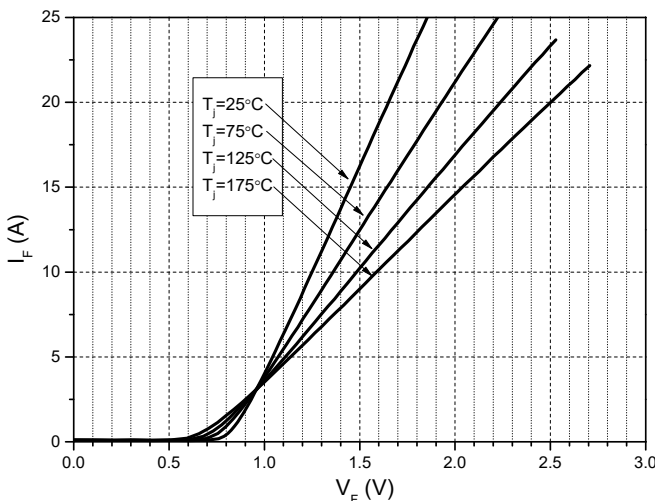


Figure 1. Forward Characteristics

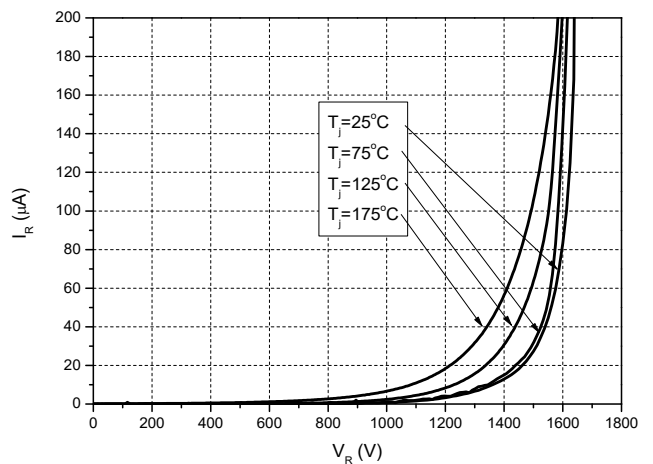


Figure 2. Reverse Characteristics

Typical Characteristics

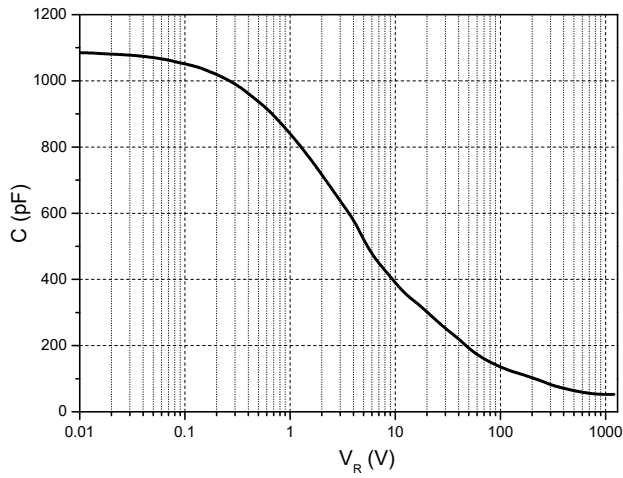


Figure 3. Capacitance vs. Reverse Voltage

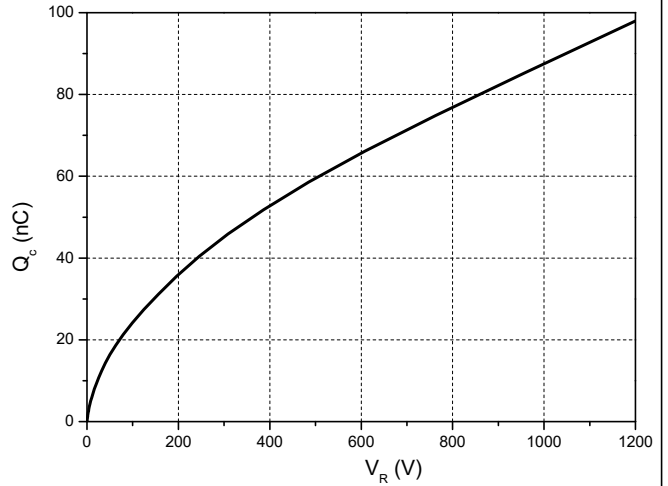


Figure 4. Total Capacitance Charge vs. Reverse Voltage

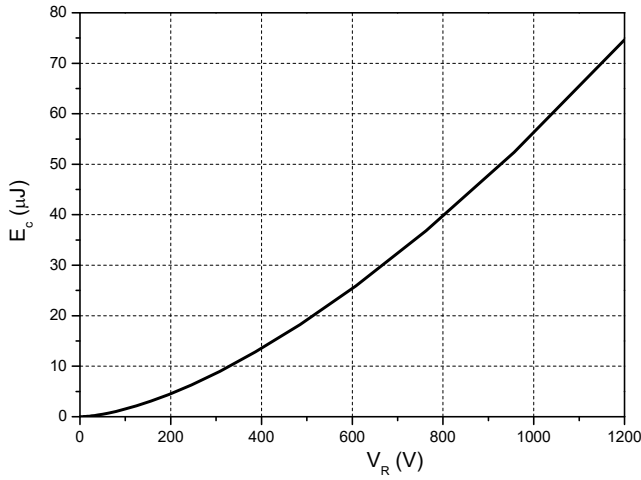


Figure 5. Capacitance Stored Energy

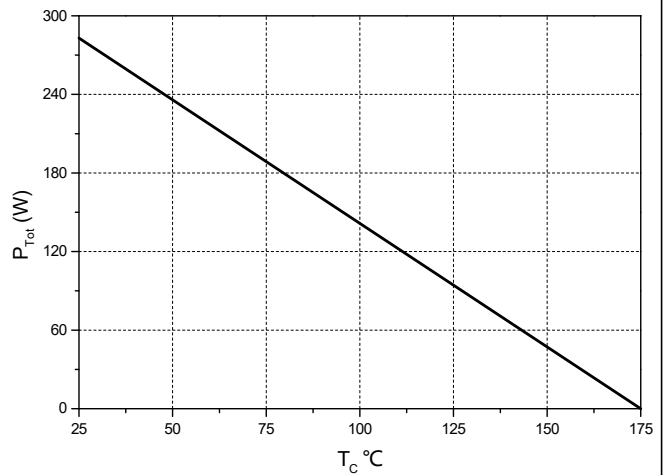


Figure 6. Power Derating

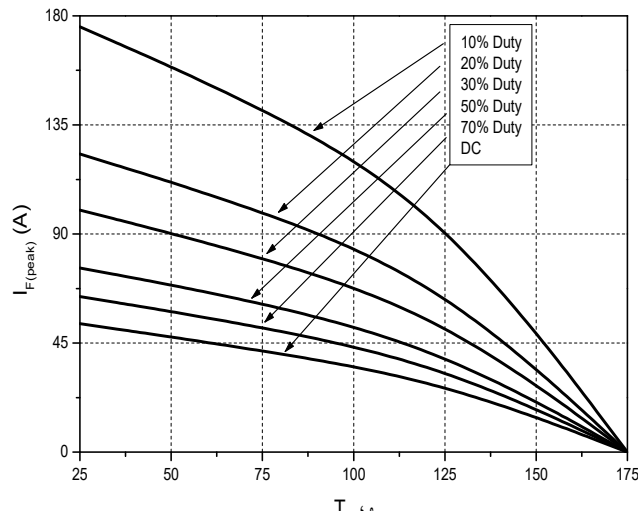


Figure 7. Current Derating

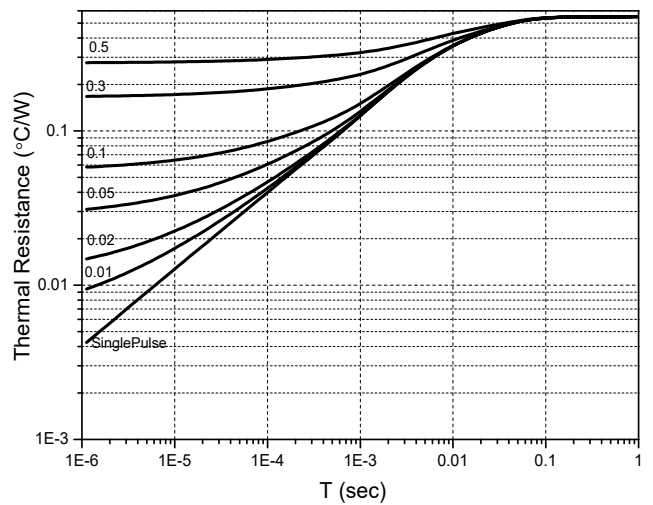


Figure 8. Transient Thermal Impedance